

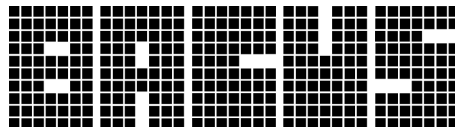
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Jed H. Rankin
Moshe E. Preil
Editors

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